



1. Cathode 2. Gate 3. Anode

TO-92 Plastic Package Weight approx. 0.18g

Rating		Symbol	Value	Unit	
Peak Repetitive Forward and Reverse Blocking					
Voltage, Note 1	MCR100-3		100	100	
(T _J =25 to 125°C, R _{GK} =1KΩ)	MCR100-4	V _{DRM}	200		
	MCR100-5	and	300	Volts	
	MCR100-6	V _{RRM}	400		
	MCR100-7		500		
	MCR100-8		600		
Forward Current RMS		I	0.8	Amps	
(All Conduction Angles)		I _{T(RMS)}			
Peak Forward Surge Current, T _{A=} 25°C		I _{TSM}	10	Amps	
(1/2 Cycle, Sine Wave, 60Hz)		ITSM			
Circuit Fusing (t=8.3ms)		l ² t	0.415	A ² s	
Peak Gate Power - Forward, T _A =25°C		P _{GM}	0.1	Watts	
Average Gate Power - Forward, T _A =25°C		P _{GF(AV)}	0.01	Watt	
Peak Gate Current - Forward, T _A =25°C		I _{GFM}	1	Amp	
(300µs,120PPS)		^I GFM			
Peak Gate Voltage - Reverse		V _{GRM}	5	Volts	
Operating Junction Temperature Range @ Rated V_{RRM} and V_{DRM}		TJ	-40 to +125	°C	
Storage Temperature Range		Ts	-40 to +150	°C	

MAXIMUM RATINGS (T_J=25°C unless otherwise noted.)

Note 1. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode.

GSP FORM A IS AVAILABLE



SEMTECH ELECTRONICS LTD. (Wholly owned subsidiary of Honey Technology Ltd.)



MCR100-3 ... MCR100-8

Characteristic	Symbol	Min	Max	Unit
Peak Forward or Reverse Blocking Current	I _{DRM} , I _{RRM}			
(V_{AK} =Rated V_{DRM} or V_{RRM})		-	10	μA
Forward "On" Voltage	V _{TM}	-	1.7	Volts
(I _™ =1A Peak @T _A =25°C)				
Gate Trigger Current(Continuous dc),Note 1	I _{GT}	-	200	μA
(Anode Voltage=7Vdc,RL=100 Ohms)				
Gate Trigger Voltage(Continuous dc)	V _{GT}	-	0.8	Volts
(Anode Voltage=7Vdc,R _L =100 Ohms)				
(Anode Voltage=Rated V_{DRM} , R _L =100 Ohms)				
Holding Current	I _H	-	5	mA
(Anode Voltage=7Vdc,initiating current=20mA)				

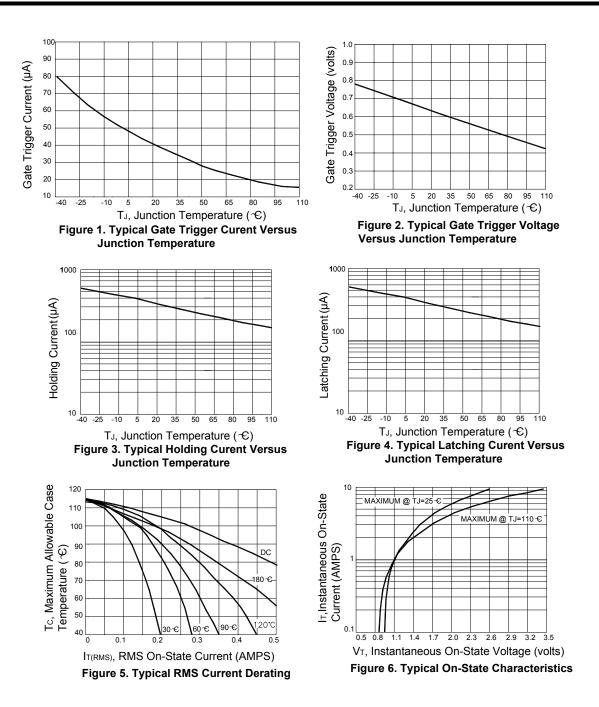
CHARACTERISTICS (T_c=25°C, R_{GK}=1K Ω unless otherwise noted.)

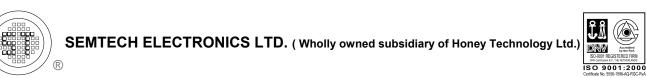
Note 1. R_{GK} current is not included in measurement.

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Dated : 06/12/2003